TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7PA05FU

Dual Inverter (open drain) with 3.6 V Tolerant Input and Output

Features

- Operating voltage range: $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High-speed operation: $t_{pd} = 3.5 \text{ ns (max)}$ at $V_{CC} = 3.0 \sim 3.6 \text{ V}$

 $t_{pd} = 4.1 \text{ ns (max) at VCC} = 2.3 \sim 2.7 \text{ V}$

 $t_{pd} = 8.2 \text{ ns (max)}$ at $V_{CC} = 1.8 \text{ V}$

High-level output current:

 $IOH/IOL = \pm 24 \text{ mA (min)}$ at VCC = 3.0 V

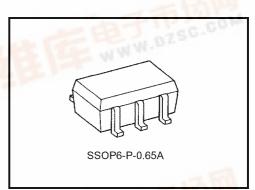
 $I_{OH}/I_{OL} = \pm 18 \text{ mA (min)}$ at $V_{CC} = 2.3 \text{ V}$

 $I_{OH}/I_{OL} = \pm 6 \text{ mA (min)}$ at $V_{CC} = 1.8 \text{ V}$

- High latch-up immunity: ±300 mA
- High ESD: Higher than or equal to ± 200 V (JEITA)

Higher than or equal to ±2000 V (MIL)

3.6-V tolerant function and power-down protection are provided on all inputs and outputs



WWW.DZSC.COM Weight: 0.0068 g (typ.)

Maximum Ratings (Ta = 25°C)

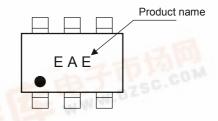
Characteristics	Symbol	Value	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	V_{IN}	-0.5~4.6	>	
		-0.5~4.6 (Note 1)		
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5 (Note 2)	>	
Input diode current	I _{IK}	-50	mA	
Output diode current	lok	±50 (Note 3)	mA	
DC output current	lout	+50	mA	
Power dissipation	P_{D}	200	mW	
DC V _{CC} /ground current	I _{CC}	±100	mA	
Storage temperature	T _{stg}	-65~150	°C	

Note 1: $V_{CC} = 0 V$

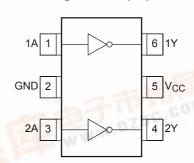
Note 2: High or Low state. The IOUT must not be exceeded maximum rating.

Note 3: Vout < GND, Vout > Vcc

Marking



Pin Assignment (top view)





Truth Table

А	Y
L	*H
Н	L

*: High-impedance

IEC Logic Symbol



Recommended Operating Conditions

Characteristics	Symbol	Value	Unit
Power supply voltage	V	1.8~3.6	V
Power supply voltage	V _{CC}	1.2~3.6 (Note 4)	V
Input voltage	V _{IN}	-0.3~3.6	V
Output voltage	V _{OUT}	0~3.6 (Note 5)	V
Output voltage	VOU1	0~V _{CC} (Note 6)	V
		+24 (Note 7)	
Output Current	l _{OL}	+18 (Note 8)	mA
		+6 (Note 9)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 10)	ns/V

Note 4: Data retention only

Note 5: $V_{CC} = 0 V$

Note 6: High or Low state

Note 7: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note 8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 9: $V_{CC} = 1.8 \text{ V}$

Note 10: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

DC Electrical Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} \leq 3.6 V)

Characteristics	Symbol	Test Condition			Min	Max	Unit		
				V _{CC} (V)					
High-Level Input Voltage	V_{IH}	-		2.7~3.6	2.0	_	V		
Low-Level Input Voltage	V_{IL}	-	_	2.7~3.6	_	0.8	v		
			$I_{OL} = 100 \mu A$	2.7~3.6	_	0.2			
Low Lovel Output Voltage	V	$V_{IN} = V_{IH}$	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	I _{OL} = 12 mA	2.7	_	0.4	· V	
Low-Level Output Voltage	V _{OL}		I _{OL} = 18 mA	3.0	_	0.4	v		
			I _{OL} = 24 mA	3.0	_	0.55			
Input Leakage Current	I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μА		
Power-off Leakage Current	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ		
Quiocoont Supply Current	laa	V _{IN} = V _{CC} or GND		2.7~3.6	_	20.0			
Quiescent Supply Current	Icc	iCC	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$			2.7~3.6	_	±20.0	μΑ
Increase in I _{CC} per Input	Δl _{CC}	$V_{IH} = V_{CC} - 0.6 V$	/	2.7~3.6	_	750			

DC Characteristics (Ta = $-40\sim85^{\circ}$ C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteristics	Symbol	Test Condition			Min	Max	Unit
	,						
High-Level Input Voltage	V _{IH}	-	_	2.3~2.7	1.6	_	V
Low-Level Input Voltage	V_{IL}	-		2.3~2.7	_	0.7	V
			I _{OL} = 100 μA	2.3~2.7	_	0.2	
Low-Level Output Voltage	V_{OL}	$V_{IN}=V_{IH} \\$	I _{OL} = 12 mA	2.3	_	0.4	V
			I _{OL} = 18 mA	2.3	_	0.6	
Input Leakage Current	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	_	±5.0	μА
Power-off Leakage Current	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА
Ouissant Cumply Current		V _{IN} = V _{CC} or GND		2.3~2.7	_	20.0	^
Quiescent Supply Current	icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3~2.7		±20.0	μА

DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteristics	Symbol	Test Condition			Min	Max	Unit
	,			V _{CC} (V)			
High-Level Input Voltage	V_{IH}	_		1.8~2.3	$\begin{array}{c} 0.7 \times \\ V_{CC} \end{array}$		V
Low-Level Input Voltage	V _{IL}	_		1.8~2.3	_	0.2 × V _{CC}	V
Low-Level Output Voltage	V	\/\/	$I_{OL} = 100 \mu A$	1.8	_	0.2	V
Low-Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$	I _{OL} = 6 mA	1.8	_	0.3	V
Input Leakage Current	I _{IN}	V _{IN} = 0~3.6 V		1.8	_	±5.0	μА
Power-off Leakage Current	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
Quiescent Supply Current		V _{IN} = V _{CC} or GND		1.8	_	20.0	^
Quiescent Supply Current	iCC	V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		1.8	_	±20.0	μА

AC Electrical Characteristics (Ta = $-40\sim85^{\circ}$ C, input t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

Characteristics	Symbol	Test Condition V _{CC} (V)		Min	Max	Unit
			1.8	1.0	8.2	ns
Propagation delay time	t _{pZL}	(Figure 1 and 2)	2.5 ± 0.2	0.8	4.1	
			3.3 ± 0.3	0.6	3.5	
	t _{pLZ}	(Figure 1 and 2)	1.8	1.0	6.8	
			2.5 ± 0.2	0.8	3.8	ns
			3.3 ± 0.3	0.6	3.5	

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Dynamic Switching Characteristics (Ta = 25°C, input $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition		TYP.	Unit		
Characteristics	Symbol	rest condition	V _{CC} (V)		Offic		
Quiet Output Maximum Dynamic		$V_{IN} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	1.8	0.25			
V _{OL}	V _{OLP}	$V_{IN} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	2.5	0.6	ns		
VOL				$V_{IN} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	3.3	0.8	
Quiet Output Minimum Dynamic		$V_{IN} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	1.8	-0.25			
V _{OL}	V _{OLV}	$V_{IN} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	2.5	-0.6	ns		
VOL		$V_{IN} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	3.3	-0.8			
Quiet Output Minimum Dynamic		$V_{IN} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	1.8	1.5			
V _{OH}	V _{OLP}	$V_{IN} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	2.5	1.9	ns		
V OH		$V_{IN} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note 11)	3.3	2.2			

Note 11: Characteristics guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

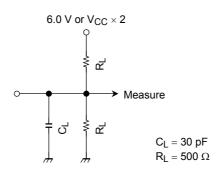
Characteristics	Symbol	Test Condition			TYP.	Unit
Characteristics	Syllibol	rest Condition		V _{CC} (V)	IIF.	5
Input Capacitance	C _{IN}	_		1.8, 2.5, 3.3	4	pF
Output Capacitance	C _{OUT}	_			3	pF
Power Dissipation Capacitance	C _{PD}	f _{IN} = 10 MHz	(Note 12)	1.8, 2.5, 3.3	4	pF

Note 12: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

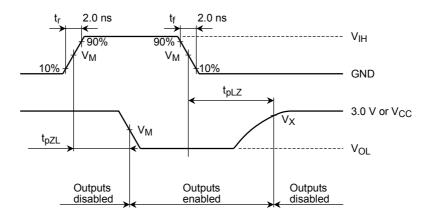
 $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$

Figure 1 Test Circuit



AC Waveforms

Figure 2 t_{pLH}, t_{pHL}



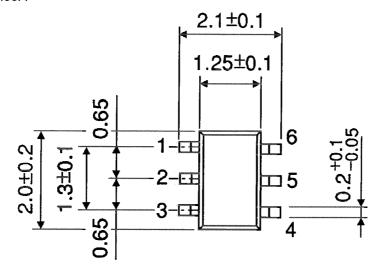
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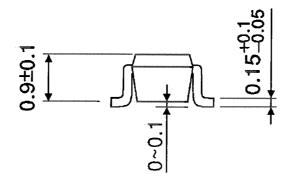
Symbol	V _{CC}							
Syllibol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V					
V _{IH}	2.7 V	V _{CC}	V _{CC}					
V _M	1.5 V	V _{CC} /2	V _{CC} /2					
VX	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V					

Package Dimensions

SSOP6-P-0.65A

Unit: mm





Weight: 0.0068 g (typ.)

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